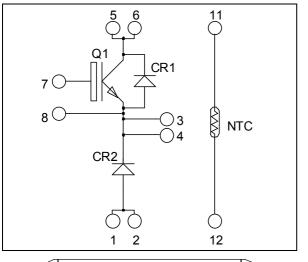
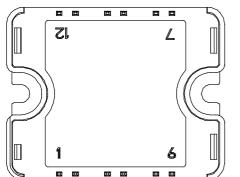


Buck chopper NPT IGBT Power Module

$V_{CES} = 1200V$ $I_{C} = 50A$ @ Tc = 80°C





Pins 1/2; 3/4; 5/6 must be shorted together

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_c = 25^{\circ}C$	75	
IC	Continuous Conector Current	$T_c = 80^{\circ}C$	50	Α
I _{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_c = 25^{\circ}C$	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	100A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_i = 25^{\circ}C$			250	μA
ICES	Zero Gate Voltage Collector Current	$V_{CE} = 1200V$	$T_{i} = 125^{\circ}C$			500	μΑ
V	Callester Emitter extension Valters	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	V
V _{CE(sat)}	Collector Emitter saturation Voltage	$I_C = 50A$	$T_{j} = 125^{\circ}C$		4.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1 \text{ mA}$		4.5		6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20 V, V_{CE} = 0V$				100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			3450		
Coes	Output Capacitance				330		pF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz			220		
Qg	Total gate Charge	$V_{GS} = 15V$			330		
Q _{ge}	Gate – Emitter Charge	$V_{Bus} = 600V$			35		nC
Q _{gc}	Gate – Collector Charge	$I_C = 50A$			200		
T _{d(on)}	Turn-on Delay Time	Inductive Switch		35			
Tr	Rise Time	$V_{GE} = 15V$			65		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 50A$ $R_{G} = 5 \Omega$			320		ns
T _f	Fall Time				30		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 50A$ $R_G = 5 \Omega$			35		ns
T _r	Rise Time				65		
T _{d(off)}	Turn-off Delay Time				360		
T _f	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_{j} = 125^{\circ}C$		6.9		mI
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 50 \text{A}$ $R_{\rm G} = 5 \ \Omega$	$T_j = 125^{\circ}C$		3.05		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V	
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			100		
IRM		v _R -1200 v	$T_{j} = 125^{\circ}C$			500	μA	
I _F	DC Forward Current		$Tc = 80^{\circ}C$		60		А	
	Diode Forward Voltage	$I_F = 60A$			2.5	3		
$V_{\rm F}$		$I_F = 120A$			3		V	
		$I_F = 60A$	$T_j = 125^{\circ}C$		1.8			
t	Reverse Recovery Time	$I_{\rm F} = 60 \text{A}$ $- V_{\rm R} = 800 \text{V}$		$T_j = 25^{\circ}C$		265		ns
t _{rr}	Reverse Recovery Time		$T_j = 125^{\circ}C$		350		115	
Q _{rr}	Reverse Recovery Charge	$di/dt = 200 \text{ A}/\mu\text{s}$	$T_j = 25^{\circ}C$		560		nC	
Qrr			$T_j = 125^{\circ}C$		2890		IIC	



Thermal and package characteristics

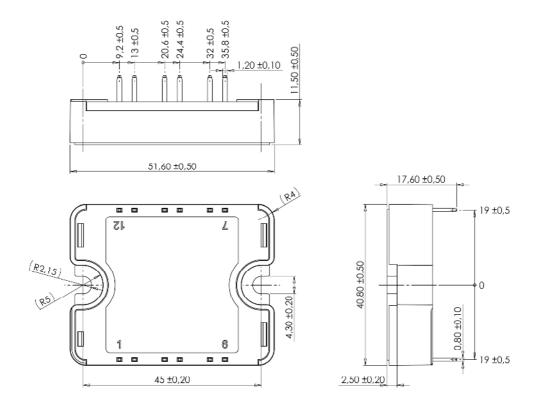
Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	IGBT			0.4	°C/W	
K _{thJC}		Diode			0.9		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature	-40		100			
Torque	Mounting torque	To heatsin	k M4	2		3	N.m
Wt	Package Weight				80	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



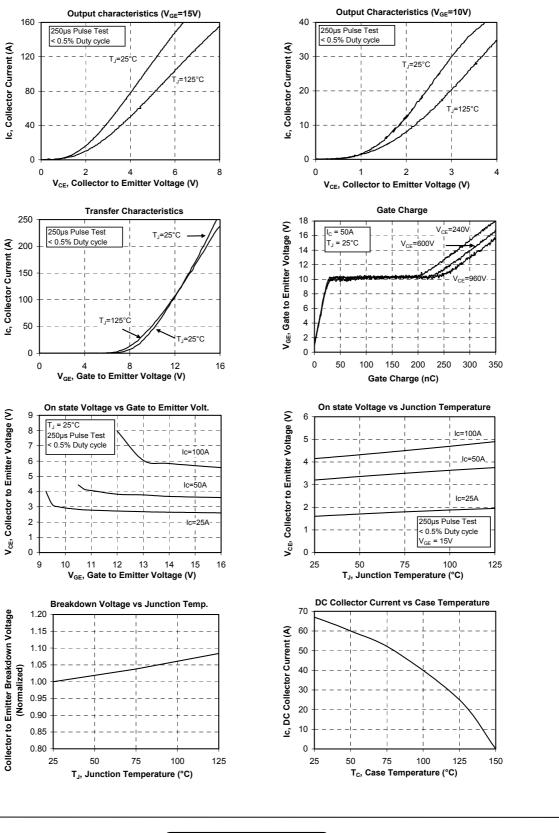
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

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Typical Performance Curve



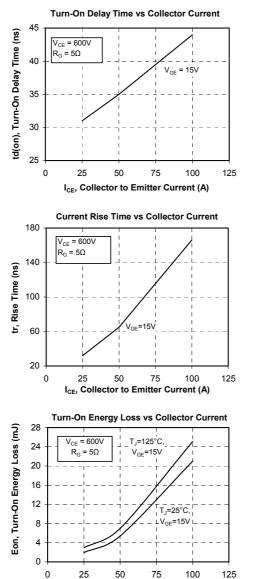
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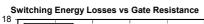
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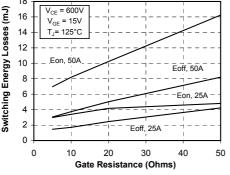
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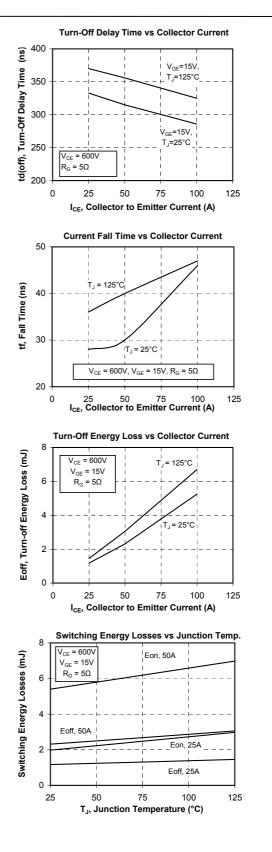




I_{CE}, Collector to Emitter Current (A)

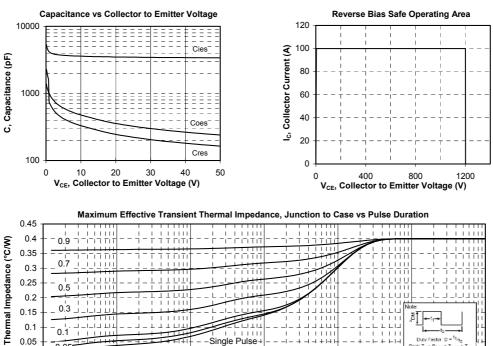


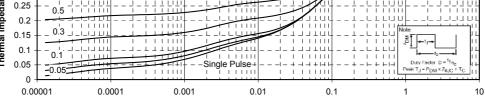
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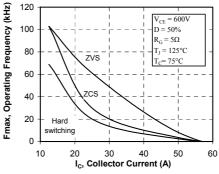








Operating Frequency vs Collector Current



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